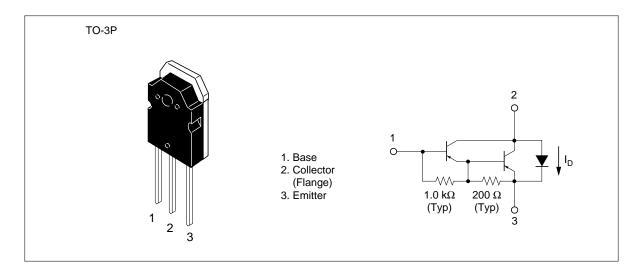
Silicon PNP Triple Diffused

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Application

Power switching complementary pair with 2SD1436(K)

Outline





Absolute Maximum Ratings $(Ta = 25^{\circ}C)$

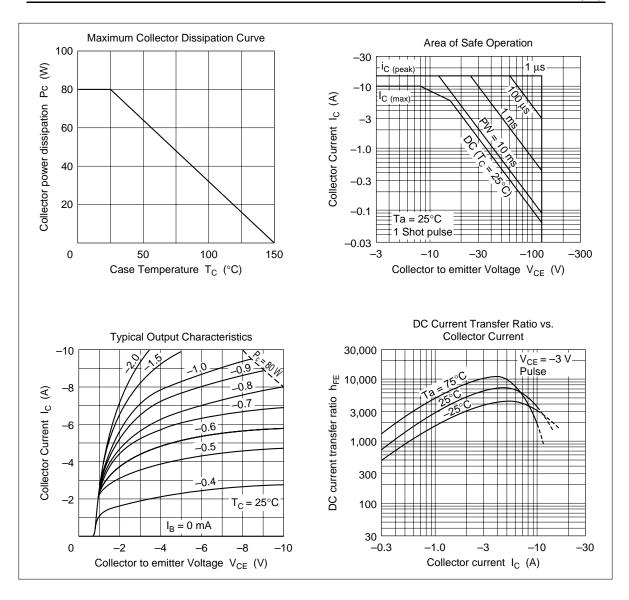
Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-120	V
Emitter to base voltage	V_{EBO}	– 7	V
Collector current	I _c	-10	A
Collector peak current	I _{C(peak)}	–15	A
C to E diode forward current	I _D *1	10	A
Collector power dissipation	P _C *1	80	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

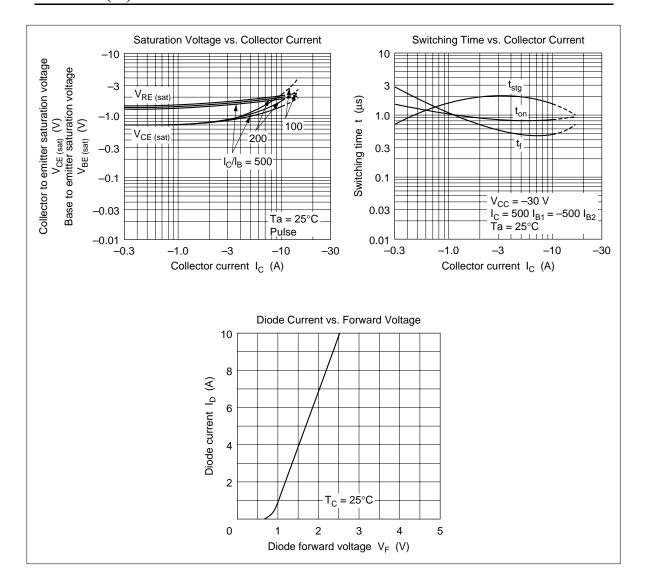
Note: 1. Value at $T_c = 25^{\circ}C$

Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{c} = -25$ mA, $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-7			V	$I_{\rm E} = -200 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-100	μA	$V_{CB} = -120 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	-10	μA	V _{CE} = -100 V, R _{BE} =
DC current transfer ratio	h _{FE}	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -5 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE(sat)1}	_	_	-1.5	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	V _{CE(sat)2}	_	_	-3.0	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
Base to emitter saturation	$V_{BE(sat)1}$	_	_	-2.0	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	$V_{\text{BE(sat)2}}$	_	_	-3.5	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
C to E diode forward voltage	V _D	_	_	3.0	V	I _D = 10 A*1
Turn on time	t _{on}	_	0.8	_	μs	$V_{cc} = -30 \text{ V},$
Turn off time	t _{off}	_	4.0	_	μs	$I_{\rm C} = -5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -10 \text{ mA}$

Note: 1. Pulse test





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